



FORM PTO-1449 LIST OF PATENTS AND OTHER DOCUMENTS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 0180151	SERIAL NO. 10/705,347
	APPLICANTS: Labelle, et al.	
	FILING DATE: November 8, 2003	GROUP ART: Unknown

U.S. PATENT DOCUMENTS							
Exam. Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
KCC	1	2003/0218223 A1	11/27/2003	Nishiyama, et al.	—	—	—
KCC	2	2003/0119334 A1	6/26/2003	Kwak, et al.	—	—	—
KCC	3	5,344,522	9/6/1994	Yagi, et al.	—	—	—
KCC	4	6,159,849	12/12/2000	Kang, et al.	—	—	—

FOREIGN PATENT DOCUMENTS								
Exam. Initials		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
KCC	1	JP 2003/249649 A	9/5/2003	Japan	—	—	abstract	only
KCC	2	JP 2003/008005 A	1/10/2003	Japan	—	—	abstract	only
KCC	3	JP 06350093 A	12/22/1994	Japan	—	—	abstract	only
KCC	4	JP 08316466 A	11/29/1996	Japan	—	—	abstract	only

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
KCC	1	Cho et al, <i>Novel Nitrogen Profile Engineering for Improved TaN/HfO₂/Si MOSFET Performance</i> , IEEE, 655-658 (December, 2001)
KCC	2	Choi et al, <i>High-Quality Ultra-thin HfO₂ Gate Dielectric MOSFETs with TaN Electrode and Nitridation Surface Preparation</i> , Digest of Technical Papers, JSAP, 15-16 (2001)

EXAMINER: KCC [Signature]	DATE CONSIDERED: 8-1-05
EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant. Information Disclosure Statement-- Section 9 PTO-1449	